Si PIN Large Sensitive Photo Diode IP-Si 103

Characteristics:

Large Sensitive Area
High Uniformity
High Responsivity
High Linearity

Applications:

Low Intensity Light detector

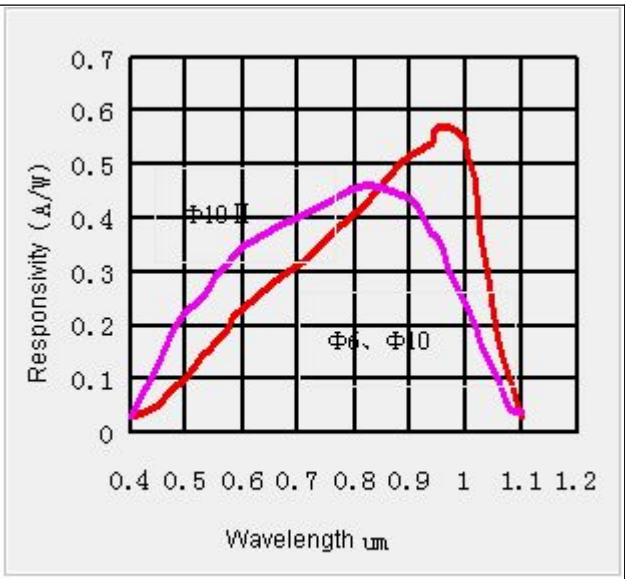
Mechanism

The large area, high sensitivity and high efficiency OE detector can be used in low optical intensity detection. The device can work under 0 voltage bias condition, equivalent as a photo cell.

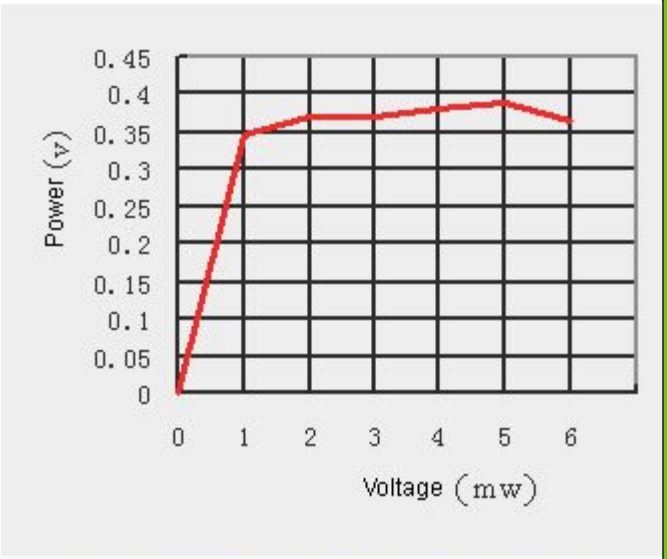
Technical Parameter (T_A=23℃)

Parameter		Symbol	Test Conditions	Typical Value			Unit
Active Area		Φ		6	10	10 II	μm
Optical	Spectrum Response Range	λ		400-1100			nm
	Responsivity	Re	V_R=0V λ=900nm	0.5		0.43	A/W
			V_R=0V λ=6328nm	0.25		0.35	
	Response Time	tr	V_R=0V	0.3	2		μS
Electrical	Dark Current	I_D	V_R=0V	30	150	150	nA
	Reverse Break Down Voltage	V_{BR}	I_R=10μA	50	30		V
	Capacitance	C_j	f=1MHz V_R=0V	200	700	1500	pF
Operating Voltage		V_R		0			V
Package			Q9 Coaxial				
Saturation Power							

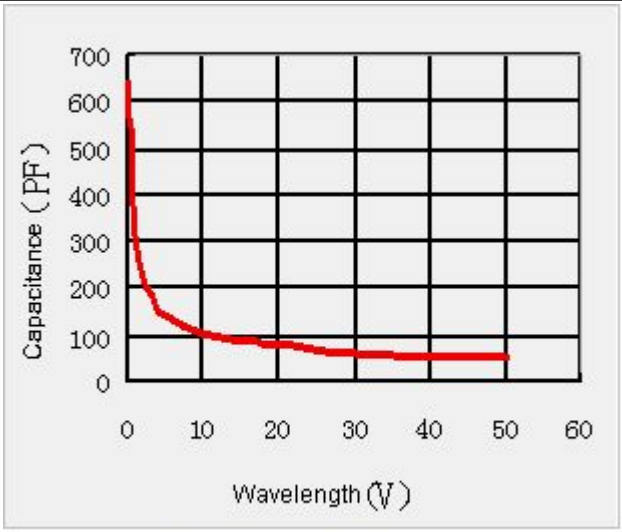
Typical Operating Characteristics



Spectrum Response Curve



Lncident Light Power VS. Opent Circuit Voltage



Capacitance VS. voltage

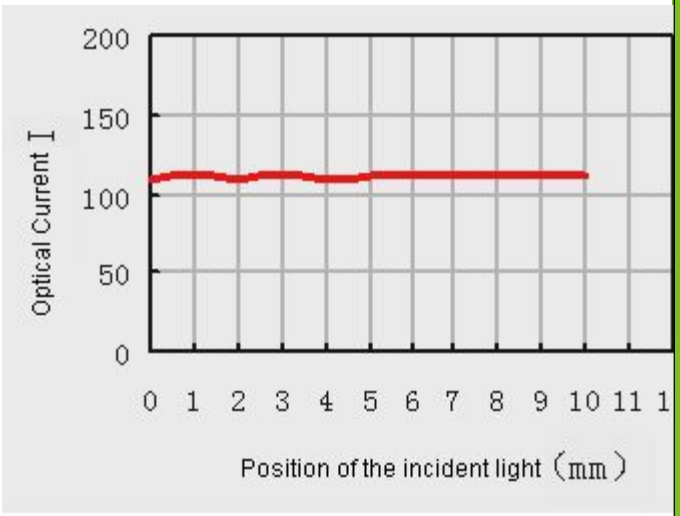
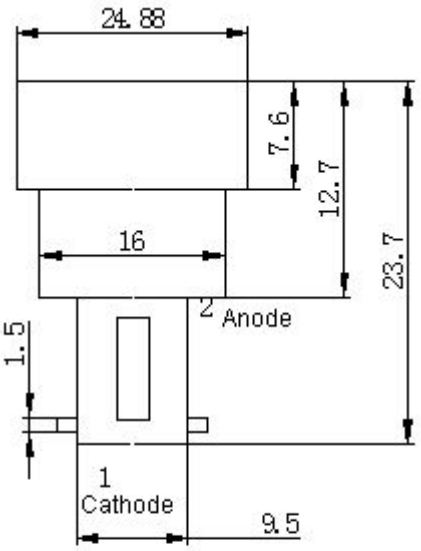


Fig. 6 Response Uniformity or the Sensitive Area

Package Information and Pin Configuration



Q9 Coaxial

Note and Usage Instruction

0 ReveIPe Bias work condition

No Vibration and shock when device operating

Static Charge Protection (Storage, Operating)